

# Katsumi Kishino

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5644610/publications.pdf>

Version: 2024-02-01

153  
papers

4,228  
citations

159525

30  
h-index

133188

59  
g-index

155  
all docs

155  
docs citations

155  
times ranked

2111  
citing authors

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 1  | Monolithically integrated green-to-orange color InGaN-based nanocolumn photonic crystal LEDs with directional radiation beam profiles. <i>Applied Physics Express</i> , 2022, 15, 022013.                                   | 1.1 | 6         |
| 2  | Photonic band characterization in InGaN/GaN nanocolumn arrays with triangular and honeycomb lattices by angle-resolved micro-photoluminescence measurements. <i>Japanese Journal of Applied Physics</i> , 2021, 60, 060904. | 0.8 | 4         |
| 3  | Graphene-Based Transparent Conducting Substrates for GaN/AlGaN Nanocolumn Flip-Chip Ultraviolet Light-Emitting Diodes. <i>ACS Applied Nano Materials</i> , 2021, 4, 9653-9664.  | 2.4 | 6         |
| 4  | Comparison of surface plasmon polariton characteristics of Ag- and Au-based InGaN/GaN nanocolumn plasmonic crystals. <i>Applied Physics Express</i> , 2021, 14, 105002.   | 1.1 | 1         |
| 5  | Energy diagram and parameters regarding localized states in InGaN/GaN nanocolumns. <i>Journal of Applied Physics</i> , 2021, 130, .   | 1.1 | 4         |
| 6  | Red-Emitting InGaN-Based Nanocolumn Light-Emitting Diodes with Highly Directional Beam Profiles. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900771.                                  | 0.8 | 6         |
| 7  | Two-dimensional multicolor (RGBY) integrated nanocolumn micro-LEDs as a fundamental technology of micro-LED display. <i>Applied Physics Express</i> , 2020, 13, 014003.   | 1.1 | 59        |
| 8  | Carrier density dependence of localized carrier recombination dynamics in orange-emitting InGaN/GaN nanocolumns. <i>Journal of Applied Physics</i> , 2020, 128, 133102.   | 1.1 | 3         |
| 9  | The influence of AlN buffer layer on the growth of self-assembled GaN nanocolumns on graphene. <i>Scientific Reports</i> , 2020, 10, 853.   | 1.6 | 8         |
| 10 | GaN/AlGaN Nanocolumn Ultraviolet Light-Emitting Diode Using Double-Layer Graphene as Substrate and Transparent Electrode. <i>Nano Letters</i> , 2019, 19, 1649-1658.  | 4.5 | 39        |
| 11 | Fabrication and optical properties of regularly arranged GaN-based nanocolumns on Si substrate. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2019, 37, 031207.                  | 0.6 | 9         |
| 12 | Column diameter dependence of the strain relaxation effect in GaN/AlGaN quantum wells on GaN nanocolumn arrays. <i>Applied Physics Express</i> , 2019, 12, 125001.  | 1.1 | 9         |
| 13 | Vertical GaN nanocolumns grown on graphene intermediated with a thin AlN buffer layer. <i>Nanotechnology</i> , 2019, 30, 015604.  | 1.3 | 21        |
| 14 | Selective area growth of InGaN-based nanocolumn LED crystals on AlN/Si substrates useful for integrated $\mu$ -LED fabrication. <i>Applied Physics Letters</i> , 2018, 112, .   | 1.5 | 23        |
| 15 | Effects of Introduction of InGaN Quantum Structures on Structural and Optical Properties of InGaN Nanocolumns. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700481.                                       | 0.7 | 1         |
| 16 | Self-Organized Eu-Doped GaN Nanocolumn Light-Emitting Diode Grown by RF-Molecular-Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 216, 1800501.                                   | 0.8 | 11        |
| 17 | Effect of structural properties on optical characteristics of InGaN/GaN nanocolumns fabricated by selective-area growth. <i>Applied Physics Express</i> , 2017, 10, 045001.   | 1.1 | 4         |
| 18 | Enhancement of light emission and internal quantum efficiency in orange and red regions for regularly arrayed InGaN/GaN nanocolumns due to surface plasmon coupling. <i>Applied Physics Letters</i> , 2017, 111, .          | 1.5 | 9         |

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 19 | Growth study of self-assembled GaN nanocolumns on silica glass by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017, 480, 67-73.   | 0.7 | 19        |
| 20 | Surface Phonons Studied by Raman Scattering in GaN Nanostructures. <i>Journal of the Physical Society of Japan</i> , 2017, 86, 074602.   | 0.7 | 8         |
| 21 | Stable-wavelength operation of europium-doped GaN nanocolumn light-emitting diodes grown by rf-plasma-assisted molecular beam epitaxy. <i>Electronics Letters</i> , 2017, 53, 666-668.   | 0.5 | 6         |
| 22 | Independent drive of integrated multicolor (RGBY) micro-LED array using regularly arrayed InGaN based nanocolumns. , 2017, , .   |     | 2         |
| 23 | Investigation of yellow/green II-VI compound semiconductor laser diode structures on InP substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 669-672.  | 0.8 | 3         |
| 24 | Spatial emission distribution and carrier recombination dynamics in regularly arrayed InGaN/GaN quantum structure nanocolumns. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 105001.  | 0.8 | 4         |
| 25 | Influence of GaN column diameter on structural properties for InGaN nanocolumns grown on top of GaN nanocolumns. <i>AIP Advances</i> , 2016, 6, .  | 0.6 | 16        |
| 26 | Spectrally-broadened multimode lasing based on structurally graded InGaN nanocolumn photonic crystals suitable for reduction of speckle contrast. <i>Applied Physics Letters</i> , 2016, 109, .  | 1.5 | 10        |
| 27 | Self-organization of dislocation-free, high-density, vertically aligned GaN nanocolumns involving InGaN quantum wells on graphene/SiO <sub>2</sub> covered with a thin AlN buffer layer. <i>Nanotechnology</i> , 2016, 27, 055302.       | 1.3 | 22        |
| 28 | Crystal structure and optical properties of a high-density InGaN nanoumbrella array as a white light source without phosphors. <i>NPG Asia Materials</i> , 2016, 8, e289-e289.   | 3.8 | 6         |
| 29 | Photon correlation study of background suppressed single InGaN nanocolumns. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 04EK03.   | 0.8 | 7         |
| 30 | Periodic Radiation Patterns and Circulating Direction of Lasing Light by Quasi Whispering Gallery Mode in Hexagonal GaN Microdisk. <i>Journal of the Physical Society of Japan</i> , 2016, 85, 053401.                                   | 0.7 | 2         |
| 31 | Application of indium tin oxide to the cladding layers of yellow/green II-VI compound semiconductor laser diode structures on InP substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 665-668. | 0.8 | 0         |
| 32 | Carrier-density dependence of photoluminescence from localized states in InGaN/GaN quantum wells in nanocolumns and a thin film. <i>Journal of Applied Physics</i> , 2015, 118, .  | 1.1 | 17        |
| 33 | GaN nanocolumn arrays with diameter <math>\approx 30\text{Å}</math>nm prepared by two-step selective area growth. <i>Electronics Letters</i> , 2015, 51, 2125-2126.  | 0.5 | 19        |
| 34 | Selective-area growth of GaN nanocolumns on Si(111) substrates for application to nanocolumn emitters with systematic analysis of dislocation filtering effect of nanocolumns. <i>Nanotechnology</i> , 2015, 26, 225602.                 | 1.3 | 130       |
| 35 | Thermally Engineered Flip-Chip InGaN/GaN Well-Ordered Nanocolumn Array LEDs. <i>IEEE Photonics Technology Letters</i> , 2015, 27, 2343-2346.   | 1.3 | 6         |
| 36 | Flip-chip bonding and fabrication of well-ordered nanocolumn arrays on sputter-deposited AlN/Si (111) substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 992-996.                               | 0.8 | 7         |

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 37 | Investigation of p-side contact layers for II-VI compound semiconductor optical devices fabricated on InP substrates by MBE. Journal of Crystal Growth, 2015, 425, 199-202.   | 0.7 | 5         |
| 38 | Monolithic integration of four-colour InGaN-based nanocolumn LEDs. Electronics Letters, 2015, 51, 852-854.  | 0.5 | 61        |
| 39 | Switching of whispering gallery mode in hexagonal GaN microdisk by change in condition of reflection surface. Electronics Letters, 2015, 51, 170-172.   | 0.5 | 1         |
| 40 | Novel selective area growth (SAG) method for regularly arranged AlGaIn nanocolumns using nanotemplates. Journal of Crystal Growth, 2015, 425, 316-321.  | 0.7 | 25        |
| 41 | Optical properties of arrays of hexagonal GaN microdisks acting as whispering-gallery-mode-type optical microcavities. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1017-1020.                            | 0.8 | 4         |
| 42 | Directional radiation beam from yellow-emitting InGaN-based nanocolumn LEDs with ordered bottom-up nanocolumn array. Applied Physics Express, 2014, 7, 112102.  | 1.1 | 37        |
| 43 | Investigation of p-contact layers for BeZnSeTe/MgZnCdSe optical devices on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1273-1277.   | 0.8 | 2         |
| 44 | Wide-range visible luminescence of ZnCdSe/BeZnTe type-II superlattices grown on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1213-1217.  | 0.8 | 1         |
| 45 | Formation of indium tin oxide transparent electrodes by magnetron sputtering for II-VI compound semiconductor optical devices on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1278-1281. | 0.8 | 0         |
| 46 | Green-Light Nanocolumn Light Emitting Diodes With Triangular-Lattice Uniform Arrays of InGaN-Based Nanocolumns. IEEE Journal of Quantum Electronics, 2014, 50, 538-547.   | 1.0 | 37        |
| 47 | Monolithic Integration of InGaN-Based Nanocolumn Light-Emitting Diodes with Different Emission Colors. Applied Physics Express, 2013, 6, 012101.  | 1.1 | 116       |
| 48 | Complex strain distribution in individual faceted InGaN/GaN nano-columnar heterostructures. Optical Materials Express, 2013, 3, 47.   | 1.6 | 9         |
| 49 | Fundamental optical properties of InN grown by epitaxial lateral overgrowth method. , 2013, , .   |     | 2         |
| 50 | Raman scattering from surface phonons in GaN nanostructures. , 2013, , .  |     | 1         |
| 51 | Photoluminescence Behaviors of Orange-Light-Emitting InGaN-Based Nanocolumns Exhibiting High Internal Quantum Efficiency (17-22%). Japanese Journal of Applied Physics, 2013, 52, 08JD09.   | 0.8 | 16        |
| 52 | 633 nm Red Emissions from InGaN Nanocolumn Light-Emitting Diode by Radio Frequency Plasma Assisted Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JE18.   | 0.8 | 25        |
| 53 | Confinement of Optical Phonons Observed by Raman Scattering in GaN/AlN Multiple Quantum Disk Nanocolumns. Journal of the Physical Society of Japan, 2013, 82, 014604.   | 0.7 | 8         |
| 54 | Two-photon absorption induced anti-Stokes emission in single InGaN/GaN quantum-dot-like objects. Physica Status Solidi - Rapid Research Letters, 2013, 7, 344-347.  | 1.2 | 2         |

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 55 | Well-arranged novel InGaN hexagonal nanoplates at the tops of nitrogen-polarity GaN nanocolumn arrays. AIP Advances, 2012, 2, .  | 0.6 | 13        |
| 56 | Optical properties of InGaN/GaN nanocolumns in yellow-to-red region. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2477-2480.   | 0.8 | 4         |
| 57 | Photoluminescence properties of selectively grown InN microcrystals. Physica Status Solidi - Rapid Research Letters, 2012, 6, 157-159.   | 1.2 | 8         |
| 58 | Low-temperature photoluminescence studies of In-rich InAlN nanocolumns. Physica Status Solidi - Rapid Research Letters, 2012, 6, 123-125.  | 1.2 | 10        |
| 59 | Breakdown of the Selection Rule of Raman Spectra in a Single GaN Nanocolumn. E-Journal of Surface Science and Nanotechnology, 2012, 10, 321-324.   | 0.1 | 3         |
| 60 | Electric Conduction in a Single GaN Nanocolumn. E-Journal of Surface Science and Nanotechnology, 2012, 10, 355-359.  | 0.1 | 0         |
| 61 | Raman Scattering from a Surface Phonon in GaN Nanowalls and Regularly-Arrayed GaN Nanocolumns. , 2011, , .   |     | 1         |
| 62 | Epitaxial lateral overgrowth of InN by rf-plasma-assisted molecular-beam epitaxy. AIP Advances, 2011, 1, 042145.   | 0.6 | 8         |
| 63 | Optically Pumped Green (530-560 nm) Stimulated Emissions from InGaN/GaN Multiple-Quantum-Well Triangular-Lattice Nanocolumn Arrays. Applied Physics Express, 2011, 4, 055001.                                  | 1.1 | 42        |
| 64 | Whispering gallery mode in periodic InGaN-based hexagonal nanoring arrays grown by rf-MBE using Ti-mask selective-area growth. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 37-40. | 0.8 | 6         |
| 65 | Formation of InGaN quantum dots in regularly arranged GaN nanocolumns grown by rf-plasma-assisted molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2374-2377.  | 0.8 | 18        |
| 66 | Dislocation reduction via selective-area growth of InN accompanied by lateral growth by rf-plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2010, 97, .  | 1.5 | 40        |
| 67 | Strain relaxation effect by nanotexturing InGaN/GaN multiple quantum well. Journal of Applied Physics, 2010, 107, .  | 1.1 | 93        |
| 68 | Emission color control from blue to red with nanocolumn diameter of InGaN/GaN nanocolumn arrays grown on same substrate. Applied Physics Letters, 2010, 96, .  | 1.5 | 359       |
| 69 | Optical properties of InGaN/GaN nanopillars fabricated by postgrowth chemically assisted ion beam etching. Journal of Applied Physics, 2010, 107, .  | 1.1 | 88        |
| 70 | Lasing Actions in GaN Tiny Hexagonal Nanoring Resonators. IEEE Photonics Journal, 2010, 2, 1027-1033.  | 1.0 | 16        |
| 71 | Energy- and density-dependent dynamics of photoexcited carriers in InN films. Applied Physics Letters, 2009, 95, .   | 1.5 | 4         |
| 72 | Positive binding energy of a biexciton confined in a localization center formed in a single disk. Physical Review B, 2009, 79, .   | 1.1 | 38        |

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 73 | Exciton and biexciton properties in GaN nanocolumn: dependence on morphology and diameter. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 141-143.  | 0.8 | 1         |
| 74 | Ti-mask selective-area growth of GaN nanorings by RF-plasma-assisted molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S607.   | 0.8 | 3         |
| 75 | Improved Ti-mask selective-area growth (SAG) by rf-plasma-assisted molecular beam epitaxy demonstrating extremely uniform GaN nanocolumn arrays. Journal of Crystal Growth, 2009, 311, 2063-2068.                                     | 0.7 | 254       |
| 76 | Photopumped green lasing on BeZnSeTe double heterostructures grown on InP substrates. Applied Physics Letters, 2009, 94, 021104.  | 1.5 | 19        |
| 77 | Selective growth of GaN nanocolumns on predeposited Al patterns by rf-plasma-assisted molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1879-1882.                                     | 0.8 | 3         |
| 78 | Effect of Be-doping on InGaN/GaN nanocolumn light-emitting diode structures by rf-plasma-assisted molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3069-3072.                         | 0.8 | 6         |
| 79 | Ultraviolet GaN-based nanocolumn light-emitting diodes grown on $\langle 111 \rangle$ Si substrates by rf-plasma-assisted molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1067-1069. | 0.8 | 40        |
| 80 | Proposal of BeZnSeTe/MgZnCdSe II-VI compound semiconductors on InP substrates for green laser diodes. , 2008, , .   |     | 1         |
| 81 | Growth and properties of InAlN nanocolumns emitting in optical communication wavelengths. , 2008, , .   |     | 0         |
| 82 | Selective-Area Growth of GaN Nanocolumns on Si(111) Substrates Using Nitrided Al Nanopatterns by RF-Plasma-Assisted Molecular-Beam Epitaxy. Applied Physics Express, 2008, 1, 015006.   | 1.1 | 37        |
| 83 | GaN/AlGaIn nanocolumn ultraviolet light-emitting diodes grown on n-(111) Si by RF-plasma-assisted molecular beam epitaxy. Electronics Letters, 2008, 44, 151.   | 0.5 | 63        |
| 84 | Lattice parameters, deviations from Vegard's rule, and E2 phonons in InAlN. Applied Physics Letters, 2008, 93, .  | 1.5 | 44        |
| 85 | InGaIn/GaN nanocolumn LEDs emitting from blue to red. , 2007, , .   |     | 94        |
| 86 | Ultrafast Intersubband Relaxation Dynamics and Coherent Nonlinearity in Bulk and Waveguide structures of GaN/AlN Multiple Quantum Wells. AIP Conference Proceedings, 2007, , .  | 0.3 | 0         |
| 87 | Structural and optical properties of GaN nanocolumns grown on (0001) sapphire substrates by rf-plasma-assisted molecular-beam epitaxy. Journal of Crystal Growth, 2007, 300, 259-262.   | 0.7 | 80        |
| 88 | Selective growth of GaN nanocolumns by Al thin layer on substrate. Physica Status Solidi (B): Basic Research, 2007, 244, 1815-1819.   | 0.7 | 29        |
| 89 | Raman Scattering in GaN/AlN Multiple Quantum Disk Nanocolumns. AIP Conference Proceedings, 2007, , .  | 0.3 | 0         |
| 90 | Origin of high oscillator strength in green-emitting InGaIn-GaN nanocolumns. Applied Physics Letters, 2006, 89, 163124.   | 1.5 | 92        |

| #   | ARTICLE   | IF  | CITATIONS |
|-----|---|-----|-----------|
| 91  | High p-type doping level of MgZnCdSe on InP substrates by inserting ZnTe thin layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 857-860.                     | 0.8 | 3         |
| 92  | Long life operations over 5000 hours of BeZnSeTe/MgZnCdSe visible light emitting diodes on InP substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 924-928.                   | 0.7 | 14        |
| 93  | Yellow-green lasing operations of ZnCdTe/MgZnSeTe laser diodes on ZnTe substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 955-958.   | 0.7 | 5         |
| 94  | Growth of high-In-content InGaN multiple quantum disk nanocolumns on Si(111) by RF plasma-assisted molecular-beam epitaxy. Physica Status Solidi (B): Basic Research, 2006, 243, 1481-1485. | 0.7 | 6         |
| 95  | High structural quality In <sup>0.75</sup> Ga <sup>0.25</sup> N multiple quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 2006, 89, 041907.                          | 1.5 | 26        |
| 96  | Raman Scattering in GaN Nanocolumns and GaN/AlN Multiple Quantum Disk Nanocolumns. E-Journal of Surface Science and Nanotechnology, 2006, 4, 227-232.                                       | 0.1 | 11        |
| 97  | Room temperature operation of 1.55-μm wavelength-range GaN/AlN quantum well intersubband photodetectors. IEICE Electronics Express, 2005, 2, 566-571.                                       | 0.3 | 7         |
| 98  | All-optical modulation using intersubband transitions at 1.55 μm in GaN/AlN multiple quantum well. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2748-2752.      | 0.8 | 1         |
| 99  | Highly efficient blue to red emissions of InGaN/GaN nano-disks integrated into GaN nanocolumns. , 2005, , .   |     | 1         |
| 100 | Lasing operation of ZnTe based yellow-green laser diodes. , 2005, , .   |     | 1         |
| 101 | Non-Polar GaN/AlN Superlattices on A-plane AlN (500nm) Buffer Layers Grown by RF-MBE. Materials Research Society Symposia Proceedings, 2004, 831, 212.                                      | 0.1 | 0         |
| 102 | Self-Organized GaN/AlN Superlattice Nanocolumn Crystals Grown by RF-MBE. Materials Research Society Symposia Proceedings, 2004, 831, 666.   | 0.1 | 3         |
| 103 | Aging characteristics of II-VI yellow light emitting diodes with beryllium chalcogenide (BeZnSeTe) active layers on InP substrates. Physica Status Solidi A, 2004, 201, 2708-2711.          | 1.7 | 7         |
| 104 | Growth and characterization of InGaN double heterostructures for optical devices at 1.5-1.7 μm communication wavelengths. Physica Status Solidi A, 2004, 201, 2850-2854.                    | 1.7 | 9         |
| 105 | Development of yellow-green LEDs and LDs using MgZnCdSe-BeZnTe superlattices on InP substrates by MBE. Physica Status Solidi (B): Basic Research, 2004, 241, 739-746.                       | 0.7 | 6         |
| 106 | Characterization of ZnCdSeTe/MgZnSeTe materials for ZnTe-based visible optical devices. Physica Status Solidi (B): Basic Research, 2004, 241, 483-486.                                      | 0.7 | 14        |
| 107 | Proposal of a novel BeZnSeTe quaternary for II-VI middle range visible light emitting devices on InP substrates. Physica Status Solidi (B): Basic Research, 2004, 241, 747-750.             | 0.7 | 11        |
| 108 | Stimulated emission from GaN nanocolumns. Physica Status Solidi (B): Basic Research, 2004, 241, 2754-2758.  | 0.7 | 52        |



| #   | ARTICLE   | IF  | CITATIONS |
|-----|---|-----|-----------|
| 109 | Yellow-green emitters based on beryllium-chalcogenides on InP substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 1477-1486.   | 0.8 | 9         |
| 110 | InGaN/GaN Multiple Quantum Disk Nanocolumn Light-Emitting Diodes Grown on (111) Si Substrate. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L1524-L1526.   | 0.8 | 351       |
| 111 | Ultrafast intersubband relaxation and nonlinear susceptibility at 1.55 $\mu\text{m}$ in GaN/AlN multiple-quantum wells. <i>Applied Physics Letters</i> , 2004, 84, 1102-1104.   | 1.5 | 91        |
| 112 | Yellow-green ZnCdSe/BeZnTe II-VI laser diodes grown on InP substrates. <i>Applied Physics Letters</i> , 2002, 81, 972-974.  | 1.5 | 36        |
| 113 | Reduction of Defect Density of ZnCdSe on InP Substrates by Introducing BeZnTe Buffer Layers. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 107-110.   | 0.7 | 5         |
| 114 | Visible Light Emitting Diode with ZnCdSe/BeZnTe Superlattices as an Active Layer and MgSe/BeZnTe Superlattices as a p-Cladding Layer. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 1001-1004.            | 0.7 | 24        |
| 115 | Refractive Index Measurements of BeZnTe and Related Superlattices on InP and Application for Waveguide Analysis of MgZnCdSe/BeZnTe Visible Lasers. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 987-990. | 0.7 | 9         |
| 116 | ZnCdTe/ZnTe Light Emitting Diodes with CdSe n-Type Contact Layers Grown on ZnTe Substrates by Molecular Beam Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 991-994.                              | 0.7 | 15        |
| 117 | Intersubband Absorption at 1.2-1.6 $\mu\text{m}$ in GaN/AlN Multiple Quantum Wells Grown by rf-Plasma Molecular Beam Epitaxy. <i>Physica Status Solidi A</i> , 2002, 192, 124-128.  | 1.7 | 7         |
| 118 | MgZnCdSe/BeZnTe Visible Light-Emitting Diode with Longer Device Lifetime over 1000 h. <i>Physica Status Solidi A</i> , 2002, 192, 201-205.  | 1.7 | 6         |
| 119 | Improved Responsivity of AlGaIn-Based Resonant Cavity-Enhanced UV Photodetectors Grown on Sapphire by RF-MBE. <i>Physica Status Solidi A</i> , 2002, 192, 292-295.  | 1.7 | 10        |
| 120 | Intersubband transition in (GaIn) <sub>m</sub> /(AlIn) <sub>n</sub> superlattices in the wavelength range from 1.08 to 1.61 $\mu\text{m}$ . <i>Applied Physics Letters</i> , 2002, 81, 1234-1236.                         | 1.5 | 167       |
| 121 | ZnCdTe/ZnTe Light Emitting Diodes with CdSe n-Type Contact Layers Grown on ZnTe Substrates by Molecular Beam Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 991-994.                              | 0.7 | 1         |
| 122 | AlGaIn Resonant Tunneling Diodes Grown by rf-MBE. <i>Physica Status Solidi A</i> , 2001, 188, 187-190.  | 1.7 | 21        |
| 123 | Resonant-Cavity-Enhanced UV Metal-Semiconductor-Metal (MSM) Photodetectors Based on AlGaIn System. <i>Physica Status Solidi A</i> , 2001, 188, 321-324.   | 1.7 | 14        |
| 124 | AlGaIn Resonant Tunneling Diodes Grown by rf-MBE. <i>Physica Status Solidi A</i> , 2001, 188, 187-190.  | 1.7 | 1         |
| 125 | Step Flow Surface Morphology in Plasma Assisted Molecular Beam Epitaxy Grown GaN. <i>Materials Research Society Symposia Proceedings</i> , 2000, 639, 3331.   | 0.1 | 0         |
| 126 | Novel II-VI Light Emitting Diodes Fabricated on InP Substrates Applying Wide-Gap and Highly p-Dopable BeZnTe for p-Cladding Layers. <i>Physica Status Solidi A</i> , 2000, 180, 37-43.                                    | 1.7 | 9         |



| #   | ARTICLE   | IF  | CITATIONS |
|-----|---|-----|-----------|
| 127 | Suppression of Inversion Domains and Decrease of Threading Dislocations in Migration Enhanced Epitaxial GaN by RF-Molecular Beam Epitaxy. <i>Physica Status Solidi A</i> , 2000, 180, 65-71.  | 1.7 | 2         |
| 128 | Self-organization of GaN/Al <sub>0.18</sub> Ga <sub>0.82</sub> N multi-layer nano-columns on (0001) Al <sub>2</sub> O <sub>3</sub> by RF molecular beam epitaxy for fabricating GaN quantum disks. <i>Journal of Crystal Growth</i> , 1998, 189-190, 138-141. | 0.7 | 96        |
| 129 | High-speed GaN growth and compositional control of GaN-AlGa <sub>n</sub> superlattice quasi-ternary compounds by RF-radical source molecular beam epitaxy. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1998, 4, 550-556.                  | 1.9 | 14        |
| 130 | Refractive index measurements of MgZnCdSe II-VI compound semiconductors grown on InP substrates and fabrications of 500-600 nm range MgZnCdSe distributed Bragg reflectors. <i>Journal of Applied Physics</i> , 1997, 81, 7575-7579.                          | 1.1 | 18        |
| 131 | Growth of Self-Organized GaN Nanostructures on Al <sub>2</sub> O <sub>3</sub> (0001) by RF-Radical Source Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1997, 36, L459-L462.   | 0.8 | 341       |
| 132 | Molecular beam epitaxial growth of MgZnCdSe on (100) InP substrates. <i>Journal of Electronic Materials</i> , 1996, 25, 425-430.  | 1.0 | 35        |
| 133 | Self-organization mechanism of GaInP quantum wires in (GaP) <sub>m</sub> /(InP) <sub>m</sub> short-period binary superlattices for GaInP/AlInP multi-quantum-wire (MQWR) lasers. <i>Optical and Quantum Electronics</i> , 1996, 28, 547-556.                  | 1.5 | 7         |
| 134 | Substrate Misorientation, Multi-Quantum Barrier, and Thermal Annealing Effects in MgZnSse and ZnCdSe Compounds and Blue-Green II-VI Light Emitting Devices. <i>Physica Status Solidi (B): Basic Research</i> , 1995, 187, 327-335.                            | 0.7 | 1         |
| 135 | Research Trends and Prospects of Blue and Ultraviolet Laser Diodes.. <i>The Review of Laser Engineering</i> , 1995, 23, 487-496.  | 0.0 | 0         |
| 136 | Refractive indices measurement of (GaInP) <sub>m</sub> /(AlInP) <sub>n</sub> quasi-ternaries and GaInP/AlInP multiple quantum wells. <i>Journal of Applied Physics</i> , 1994, 76, 1809-1818.   | 1.1 | 40        |
| 137 | 600-nm wavelength range GaInP/AlInP quasi-ternary compounds and lasers prepared by gas-source molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 1993, 74, 819-824.  | 1.1 | 25        |
| 138 | Remarkable reduction of threshold current density by substrate misorientation effects in 660 nm visible light lasers with GaInP bulk active layers. <i>Applied Physics Letters</i> , 1992, 60, 1046-1048.   | 1.5 | 21        |
| 139 | Enhanced carrier confinement effect by the multi-quantum barrier in 660 nm GaInP/AlInP visible lasers. <i>Applied Physics Letters</i> , 1991, 58, 1822-1824.  | 1.5 | 80        |
| 140 | High-Optical-quality GaInP and GaInP/AlInP double heterostructure lasers grown on GaAs substrates by gas-source molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 1989, 66, 4557-4559.  | 1.1 | 22        |
| 141 | Fabrication and lasing characteristics of 0.67 μm GaInAsP/AlGaAs visible lasers prepared by liquid phase epitaxy on. <i>IEEE Journal of Quantum Electronics</i> , 1987, 23, 180-187.  | 1.0 | 13        |
| 142 | Substrate Misorientation Effect On Cubic And Hexagonal GaN Grown On GaAs By Molecular Beam Epitaxy Using RF-radical Nitrogen Source. , 0, , .   |     | 0         |
| 143 | Room temperature CW operation of GaInP/AlGaInP multiple quantum wire visible lasers (MQWR-LD). , 0, , .   |     | 2         |
| 144 | Molecular beam epitaxial growth of MgZnCdSe on (100) InP substrates. , 0, , .   |     | 0         |

| #   | ARTICLE  | IF  | CITATIONS |
|-----|--|-----|-----------|
| 145 | Effect of (GaP)/sub m/(InP)/sub m/ short period binary superlattice period on quantum wire formation by strain induced lateral layer ordering in GaInP/AlInP multi-quantum-wire lasers. , 0, , . |     | 0         |
| 146 | Quasi-free standing GaN epitaxial layer grown on nano-columnar GaN by RF-plasma assisted molecular beam epitaxy. , 0, , .  |     | 0         |
| 147 | Room temperature negative differential resistance in AlN/GaN double barrier resonant tunneling diodes grown by RF-plasma assisted molecular beam epitaxy. , 0, , .                               |     | 2         |
| 148 | Yellow-green lasing emission from ZnCdSe/BeZnTe II-VI laser diodes on InP substrates. , 0, , .   |     | 0         |
| 149 | High-quality InN grown by RF-plasma assisted molecular beam epitaxy as novel materials for optical communication. , 0, , .   |     | 0         |
| 150 | Ultrafast intersubband relaxation at 1.55 $\mu\text{m}$ in GaN/AlN MQWs. , 0, , .  |     | 0         |
| 151 | Middle-range visible light emitting devices fabricated using BeZnSeTe/MgZnCdSe II-VI compounds on InP substrates. , 0, , .   |     | 0         |
| 152 | Ultrafast intersubband relaxation dynamics in GaN/AlN multiple quantum wells using two-color pump-probe technique. , 0, , .  |     | 0         |
| 153 | Ti-mask Selective-Area Growth of GaN by RF-Plasma-Assisted Molecular-Beam Epitaxy for Fabricating Regularly Arranged InGaN/GaN Nanocolumns. Applied Physics Express, 0, 1, 124002.               | 1.1 | 179       |